Preferred Device

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed for use in solid state relays, MPU interface, TTL logic and other light industrial or consumer applications. Supplied in surface mount package for use in automated manufacturing.

Features

- Sensitive Gate Trigger Current in Four Trigger Modes
- Blocking Voltage to 600 Volts
- Glass Passivated Surface for Reliability and Uniformity
- Surface Mount Package
- Pb–Free Packages are Available

MAXIMUM RATINGS ($T_J = 25^{\circ}C$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|---------------------------------------|-------------|------------------|
| $\begin{tabular}{lllllllllllllllllllllllllllllllllll$ | V _{DRM,} V _{RRM} | 200 600 | V |
| On–State Current RMS ($T_C = 80^{\circ}C$) (Full Sine Wave 50 to 60 Hz) | I _{T(RMS)} | 0.8 | A |
| Peak Non-repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_C = 25^{\circ}C$) | I _{TSM} | 8.0 | A |
| Circuit Fusing Considerations (Pulse Width = 8.3 ms) | l ² t | 0.4 | A ² s |
| Peak Gate Power $(T_C = 80^{\circ}C, Pulse Width \le 1.0 \mu s)$ | P _{GM} | 5.0 | W |
| Average Gate Power $(T_C = 80^{\circ}C, t = 8.3 \text{ ms})$ | P _{G(AV)} | 0.1 | W |
| Operating Junction Temperature Range | TJ | -40 to +110 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

 V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

THERMAL CHARACTERISTICS

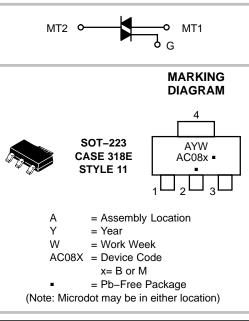
| Characteristic | Symbol | Max | Unit |
|--|-----------------|-----|------|
| Thermal Resistance, Junction-to-Ambient PCB Mounted per Figure 1 | $R_{\theta JA}$ | 156 | °C/W |
| Thermal Resistance, Junction-to-Tab Measured on MT2 Tab Adjacent to Epoxy | $R_{\theta JT}$ | 25 | °C/W |
| Maximum Device Temperature for Soldering Purposes for 10 Secs Maximum | ΤL | 260 | °C |



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TRIAC 0.8 AMPERE RMS 200 thru 600 VOLTS



| PIN ASSIGNMENT | | | | |
|----------------|-----------------|--|--|--|
| 1 | Main Terminal 1 | | | |
| 2 | Main Terminal 2 | | | |
| 3 | Gate | | | |
| 4 | Main Terminal 2 | | | |
| | | | | |

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-----------|----------------------|-----------------------|
| MAC08BT1 | SOT-223 | 1000 Tape & Reel |
| MAC08BT1G | SOT-223 (Pb-Free) | 1000 Tape & Reel |
| MAC08MT1 | SOT-223 | 1000 Tape & Reel |
| MAC08MT1G | SOT-223 (Pb-Free) | 1000 Tape & Reel |

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

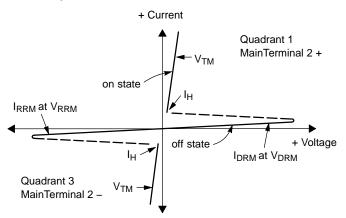
Preferred devices are recommended choices for future use and best overall value.

| Characteristic | | | Min | Тур | Max | Unit |
|---|---|--|-----|-----|-----------|----------|
| DFF CHARACTERISTICS | | • | | | | |
| Peak Repetitive Blocking Current (V_D = Rated V_{DRM} , V_{RRM} ; Gate Open) | T _J = 25°C T _J = 110°C | I _{DRM} , I _{RRM} | | | 10 200 | μΑ μΑ |
| ON CHARACTERISTICS | | | - | - | <u> </u> | |
| Peak On–State Voltage (Note 2) ($I_T = \pm 1.1 \text{ A Peak}$) | V _{TM} | - | - | 1.9 | V | |
| Gate Trigger Current (Continuous dc) All Quadrants (V _D = 12 Vdc, R _L = 100 Ω) | I _{GT} | - | - | 10 | mA | |
| Holding Current (Continuous dc) ($V_D = 12$ Vdc, Gate Open, Initiating Current = ± 20 mA) | | | - | - | 5.0 | mA |
| Gate Trigger Voltage (Continuous dc) All Quadrants $(V_D = 12 \text{ Vdc}, R_L = 100 \Omega)$ | | | - | - | 2.0 | V |
| OYNAMIC CHARACTERISTICS | | | | | | |
| Critical Rate of Rise of Commutation Voltage (f = 250 Hz, I_{TM} = 1.0 A, Commutating di/dt = 1.5 A/mS On–State Current Duration = 2.0 mS, V_{DRM} = 200 V, Gate Unenergized, T_C = 110°C, Gate Source Resistance = 150 Ω , See Figure 10) | (dv/dt) _c | 1.5 | - | _ | V/µs | |
| Critical Rate–of–Rise of Off State Voltage (V _{pk} = Rated V _{DRM} , T _C = 110°C, Gate Open, Exponential Method) | | | 10 | - | - | V/µs |

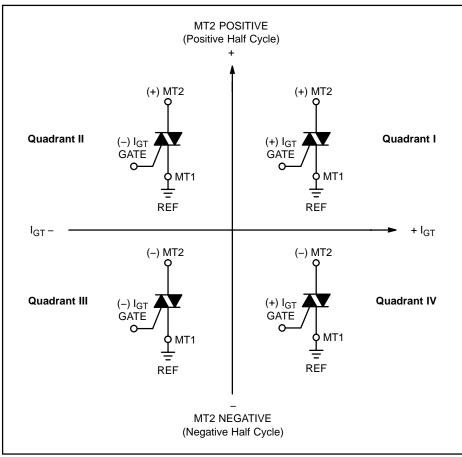
2. Pulse Test: Pulse Width \leq 300 µsec, Duty Cycle \leq 2%.

Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|------------------|---|
| V _{DRM} | Peak Repetitive Forward Off State Voltage |
| I _{DRM} | Peak Forward Blocking Current |
| V _{RRM} | Peak Repetitive Reverse Off State Voltage |
| I _{RRM} | Peak Reverse Blocking Current |
| V _{TM} | Maximum On State Voltage |
| Ι _Η | Holding Current |

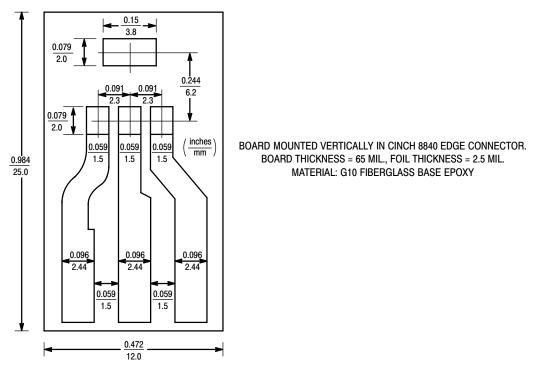


Quadrant Definitions for a Triac

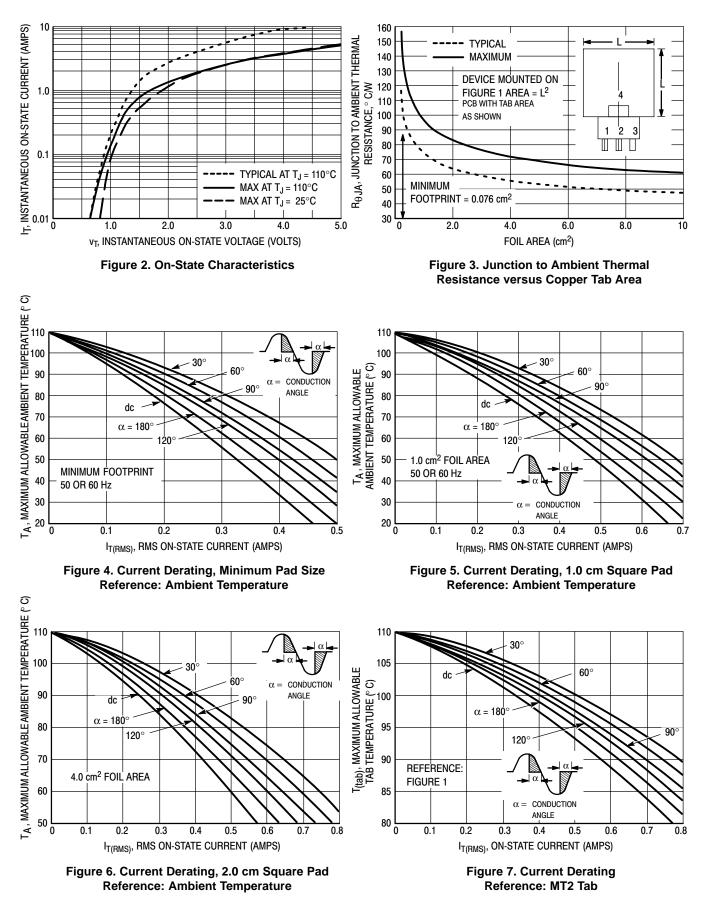


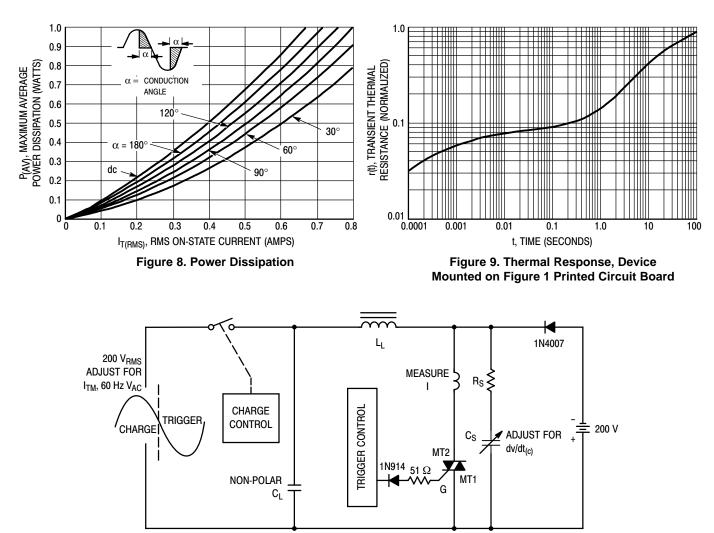
All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



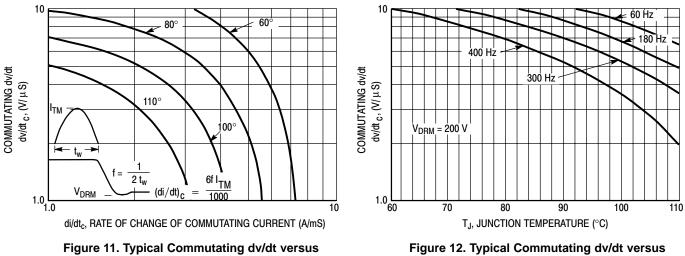






Note: Component values are for verification of rated (dv/dt)_c. See AN1048 for additional information.

Figure 10. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Voltage (dv/dt)_c



Current Crossing Rate and Junction Temperature

Figure 12. Typical Commutating dv/dt versus Junction Temperature at 0.8 Amps RMS

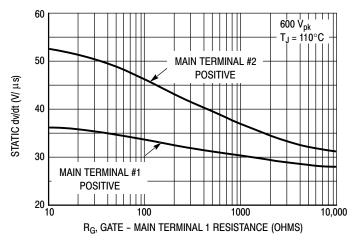


Figure 13. Exponential Static dv/dt versus Gate – Main Terminal 1 Resistance

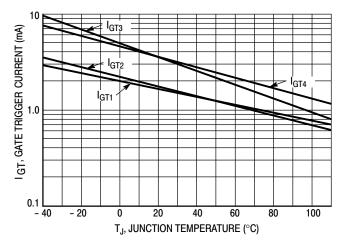


Figure 14. Typical Gate Trigger Current Variation

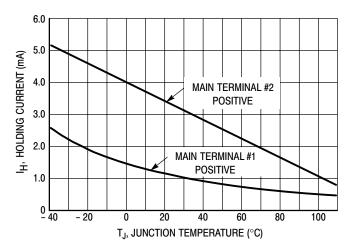


Figure 15. Typical Holding Current Variation

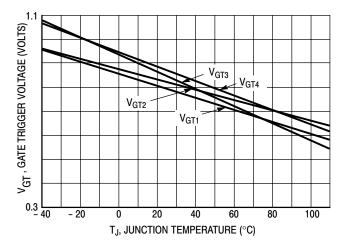
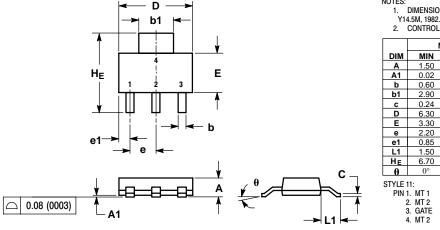


Figure 16. Gate Trigger Voltage Variation

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE L

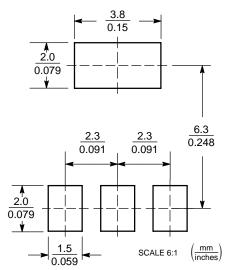


NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI X14 5M 1982

2. CONTROLLING DIMENSION: INCH.

| | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|--------|-------|-------|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| Α | 1.50 | 1.63 | 1.75 | 0.060 | 0.064 | 0.068 |
| A1 | 0.02 | 0.06 | 0.10 | 0.001 | 0.002 | 0.004 |
| b | 0.60 | 0.75 | 0.89 | 0.024 | 0.030 | 0.035 |
| b1 | 2.90 | 3.06 | 3.20 | 0.115 | 0.121 | 0.126 |
| с | 0.24 | 0.29 | 0.35 | 0.009 | 0.012 | 0.014 |
| D | 6.30 | 6.50 | 6.70 | 0.249 | 0.256 | 0.263 |
| E | 3.30 | 3.50 | 3.70 | 0.130 | 0.138 | 0.145 |
| е | 2.20 | 2.30 | 2.40 | 0.087 | 0.091 | 0.094 |
| e1 | 0.85 | 0.94 | 1.05 | 0.033 | 0.037 | 0.041 |
| L1 | 1.50 | 1.75 | 2.00 | 0.060 | 0.069 | 0.078 |
| HE | 6.70 | 7.00 | 7.30 | 0.264 | 0.276 | 0.287 |
| θ | 0° | - | 10° | 0° | - | 10° |

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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